PCN Nu	mber:		20220622	000.2			PCN [	Date:	Jur	ne 28, 2022	
Title:	Quali	fication of [	OMOS6 as	an additio	nal Wafer	Fab site op	tion fo	or selec	t device	es	
Custom	er Contac	:t:	<u>PCN</u>	<u>Manager</u>			Dept:			ality Services	
Propose	ed 1 <sup>st</sup> Ship	Date:	Dec 2	28, 2022		Sample accepte			Jul	y 28, 2022	
	*5	Sample red	quests rec	eived aft	er (July	28, 2022)	will n	ot be	suppor	ted.	
Change	Type:										
	sembly Site	<u>e</u>		Assembly						ly Materials	
	sign			Electrical						ical Specification	
	st Site			Packing/S					Test Pro		
	fer Bump S			Wafer Bui						Bump Process	
	fer Fab Sit	.e		Wafer Fat Part numl					warer r	ab Process	
					CN Deta						
Descrin	tion of Ch	ange:		<u> </u>	CN DEL	1115					
			to announ	ce the qua	lification	of DMOS6	and Ch	enadu	Probe a	s additional sources	
	ent Fab	Proce		Wafer		itional Fa		Proce		Wafer Diameter	
	Site			Diameter		Site					
R	FAB	LBC	)	300 mm		DMOS6		LBC	9	300 mm	
	_	_									
Cu	rrent Prob			onal Prob							
	CLARK-F	'K	CD-	PR (Cheng	jau)						
Reason	for Chang	ge:									
Continui	ty of Supp	lv									
	<u> </u>	ct on Forn	a Eit Eus	etion Ou	ality or l	) aliability	(nocil	biyo / s		<b>(0)</b>	
None	ateu iiipa	Ct On Form	ii, Fit, Fuii	iction, Qu	anty or i	Kenability	(posit	LIVE / I	legativ	<i>(e)</i> .	
	- 4			Line C		OCN.					
_		uct identifi	ication re	suiting tr	om tnis i	CN:					
Curren		T at t at:		. (00)	011 011				01.1.01		
<del> </del>	t Chip Site	Chip Site	Origin Co	de (20L)	Chip Site Country Code (21L) Chip Site City						
	RFAB		RFB	ίFB			USA Richardson			dson	
New Fa		Claire Cite	Outsia Ca	d- (20L)	Chin Cit	C	Country Code (211) Chin Site City				
I	New Chip Site Chip Site Orio			ae (20L)	Cnip Site	te Country Code (21L) Ch				hip Site City  Dallas	
1		inning Jaha	DM6	al product	lahal)	USA			Dai	idS	
Sample product shipping label (not actual product label)											
TE	EXAS UMENTS	Pub			(1B) C	1741 CA7N	C D				
		G4	44.3			174LS07N		00			
2DC:											
MSL 2 /260C/1 YEAR SEAL DT											
OPT: (P)											
LBL: 5A (L)T0:1750 (20L) CSO: SHE (21L) CCO: USA (22L) ASO: MLA (23L) ACO: MYS											
Product Affected:											
SN1805	032RHBR	TPS25830Q	WRHBRQ1	TPS25832	QWRHBRO	1 TPS258	40QWF	RHBTQ1	TPS25	5846QWRHBRQ1	
	032RHBT	TPS25830Q			QWRHBTO			RHBRQ1		5846QWRHBTQ1	
										·	
	001RHBT										
SN18050 SN18050 SN20040	t Affected 032RHBR 032RHBT 001RHBR	TPS25830Q TPS25830Q TPS25831Q	WRHBTQ1 WRHBRQ1	TPS25832 TPS25833	QWRHBRO QWRHBTO QWRHBRO	1 TPS258 1 TPS258 21 TPS258	40QWF 40QWF 42QWF	RHBTQ1 RHBRQ1 RHBRQ1			
SN2004	001RHBT	TPS25831Q	WRHBTQ1	TPS25833	BQWRHBTO	(1   TPS258	42QWF	RHBTQ1			

# **Automotive New Product Qualification Summary**

(As per AEC-Q100 and JEDEC Guidelines)
Approved 25-March-2022

### **Product Attributes**

Attributes	Qual Device: TPS25831QWRHBRQ1	Qual Device: TPS25830QWRHBRQ1	QBS Process Reference: <u>LMR33630CQRNXRQ1</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40C to 125C
Product Function	Power Management	Power Management	Power Management
Wafer Fab Supplier	DMOS6	DMOS6	DMOS6
Die Revision	В0	В0	B0
Assembly Site	NSE (UTAC)	NSE (UTAC)	CDAT
Package Type	QFN	QFN	QFN-HR
Package Designator	RHB	RHB	RNX
Ball/Lead Count	32	32	12

<sup>-</sup> QBS: Qual By Similarity

## **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: TPS25831QWRHBRQ 1	Qual Device: <u>TPS25830QWRHBRQ</u> <u>1</u>	QBS Process Reference: LMR33630CQRNXRQ1
					Test Group	A – Accelerate	ed Environment Stress Te	sts	
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Automotive Preconditioni ng Level 2	168 Hours, 85C/60 % RH	3/969/0	1/77/0	3/693/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	-	3/231/0
uHAS T	А3	JEDEC JESD22- A102	3	77	UnBiased HAST, 130C/85%RH	96Hours	-	-	3/231/0
AC	А3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 Hours	3/231/0	-	-
TC	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, - 65/150C	500 Cycles	3/231/0	1/77/0	3/231/0

<sup>-</sup> Qual Devices TPS25831WQRHBRQ1 and TPS25830WQRHBQ1 are qualified at LEVEL2-260C

Typ e	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: TPS25831QWRHBRQ 1	Qual Device: <u>TPS25830QWRHBR</u> <u>Q 1</u>	QBS Process Reference: LMR33630CQRNXRQ1
WB P	C2	MIL- STD88 3 Metho d 2011	1	5	After TC Wire Bond Pull (Cpk>1.67)	-	1/5/0	1/5/0	-
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle, - 40/125C	1000 Cycles	1/45/0	-	1/44/0 (Note 1)
HTS L	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 150C	1000 Hours	3/231/0	-	3/231/0
HTO L	B1	JEDEC JESD22- A108	3	77	Life Test, 125C	1000 Hours	3/231/0		3/231/0
ELF R	B2	AEC Q100- 008	3	800	Early Life Failure Rate, 125C	48 Hours	1/800/0	-	3/2400/0
EDR	В3	AEC Q100- 005	3	77	NVM Endurance, Data Retention, and Operational Life	-	3/231/0 (Note 2)	-	3/231/0
						p C – Package	Assembly Integrity Tes	sts	
WB S	C1	AEC Q100- 001	1	30	Wire Bond Shear (Cpk>1.67)	-	1/30/0	-	-
WB P	C2	MIL- STD88 3 Metho d 2011	1	30	Wire Bond Pull (Cpk>1.67)	-	1/30/0	-	-
SD	СЗ	JEDEC JESD22- B102	1	15	Pb Free Surface Mount Solderability	Pb Free/Solde r-	1/15/0	-	1/15/0
SD	C3	JEDEC JESD22- B102	1	15	Surface Mount Solderability >95% Lead Coverage	-	1/15/0	-	-
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	3/30/0	-	3/90/0
					Test Gro	up D – Die Fal	prication Reliability Test	s	
EM	D1	JES D61	-	-	Electromigrati on	-	-	-	Completed per Process Technology Requirements
TDD B	D2	JES D35	-	-	Time Dependent Dielectric Breakdown	-	-	-	Completed per Process Technology Requirements

HCI	D3	JESD6 0 & 28	-	-	Hot Injection Carrier	-	-	-	Completed per Process Technology Requirements
NBT I	D4	-	1	1	Negative Bias Temperature Instability	-	-	-	Completed per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	-	Completed per Process Technology Requirements
					Test G	roup E – Elect	trical Verification Tests		
HBM	E2	AEC Q100- 002	1	3	ESD - HBM - Q100	2000 V	3/9/0	1/3/0	1/3/0
HBM	E2	AEC Q100- 002	1	3	ESD - HBM - Q100	4000 V	3/9/0	1/3/0	-
CD M	E3	AEC Q100- 011	1	3	ESD - CDM - Q100	750 V	3/9/0	1/3/0	1/3/0

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: TPS25831QWRHBRQ1	Qual Device: TPS25830QWRHBR Q 1	QBS Process Reference: LMR33630CQRNXRQ1
CDM	E3	AEC Q100- 011	1	3	ESD - CDM - Q100	1000 V	3/9/0	1/3/0	-
LU	E4	AEC Q100- 004	1	6	Latch-up	Per AEC Q100-004	3/18/0	1/3/0	-
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67	3/90/0	1/30/0	-

### Note:

One (1) reject was attributed to test issue and was discounted. FA Report attached to eQDB: 20190614-130319 and 20190521-129951

HTSL data extended as Data Retention

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C

Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
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WW PCN Team	PCN www admin_team@list.ti.com
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